

SANYO Semiconductors DATA SHEET

2SA2043 PNP Epitaxial Planar Silicon Transistor DC / DC Converter Applications

Applications

· Relay drivers, lamp drivers, motor drivers, flash.

Features

- · Adoption of FBET and MBIT processes.
- · Large current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.
- · High allowable power dissipation.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		-15	V
Collector-to-Emitter Voltage	VCEO		-15	V
Emitter-to-Base Voltage	VEBO		-5	V
Collector Current	IC		-10	Α
Collector Current (Pulse)	ICP		-13	Α
Base Current	IΒ		-1.2	Α
Collector Dissipation	Do		1	W
	PC	Tc=25°C	15	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =-12V, I _E =0A			-0.1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =-4V, I _C =0A			-0.1	μΑ
DC Current Gain	hFE	VCE=-2V, IC=-500mA	200		560	
Gain-Bandwidth Product	fT	VCE=-2V, IC=-500mA		220		MHz
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		90		pF

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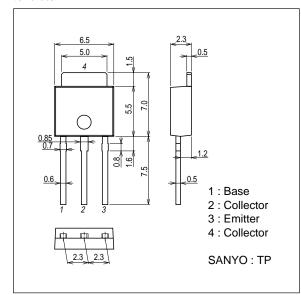
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)1	IC=-3A, IB=-60mA		-110	-170	mV
	VCE(sat)2	IC=-4.5A, IB=-90mA		-160	-240	mV
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=-3A, IB=-60mA		-0.85	-1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=-10μA, IE=0A	-15			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=-1mA, RBE=∞	-15			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	IE=-10μA, IC=0A	-5			V
Turn-On Time	ton	See specified test circuit.		30		ns
Storage Time	tstg	See specified test circuit.		120		ns
Fall Time	tf	See specified test circuit.		14		ns

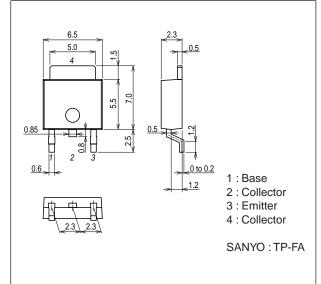
Package Dimensions

unit : mm (typ) 7518-003

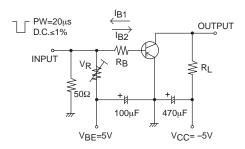


Package Dimensions

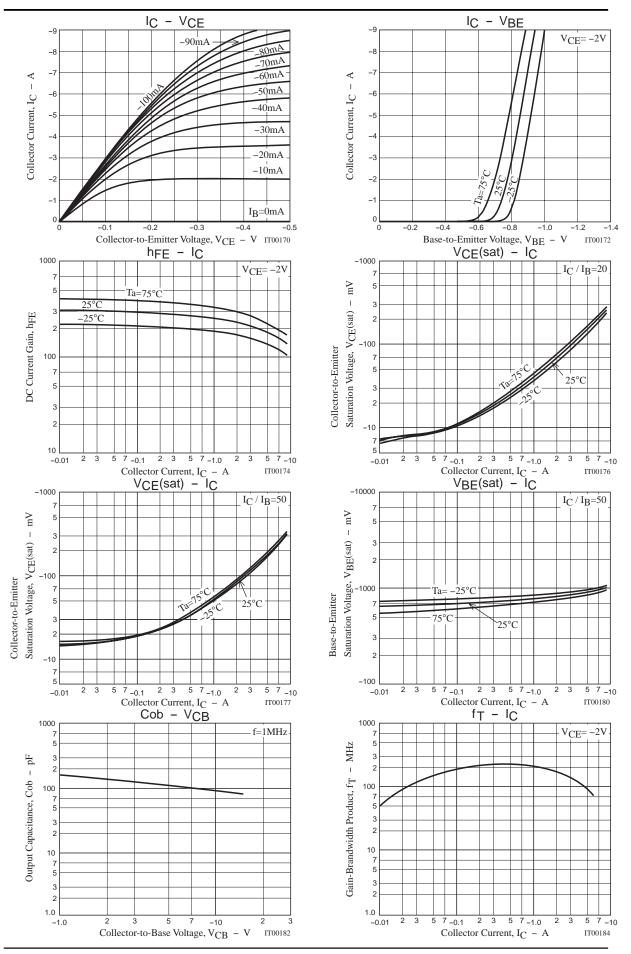
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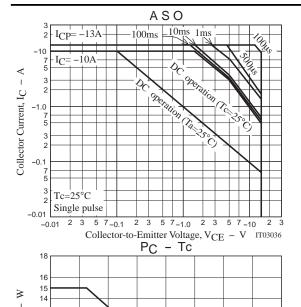


Switching Time Test Circuit



$$I_{C} = -20I_{B1} = 20I_{B2} = -3A$$

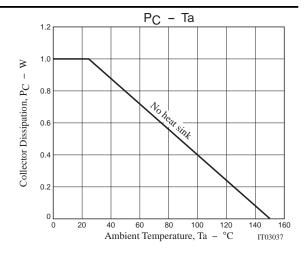




Case Temperature, Tc -

°C

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Collector Dissipation, PC

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